



Let's go **GaNFast™**

GaN Power IC Adoption Takes Off in Fast Charging Market

APEC 2019 PowerAmerica IS19, March 21, 2019

"Advances in the Adoption of Wide Bandgap Semiconductors in Commercial and Industrial Applications"

Dan Kinzer, COO/CTO Navitas

Dan.kinzer@navitassemi.com

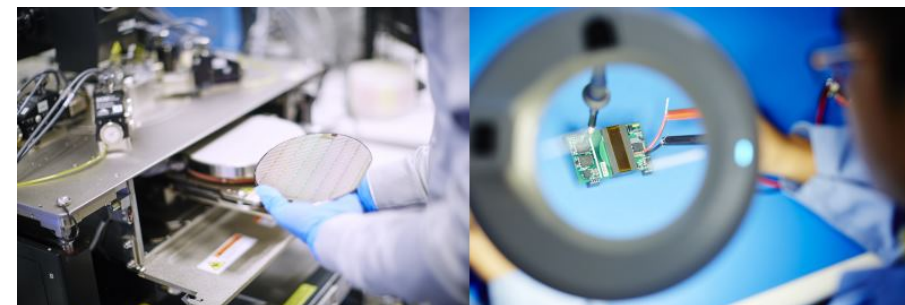


Navitas Semiconductor



GaNFast™

- World's first GaN power IC company
 - JEDEC qualified
 - Volume production with fast ramp
- Navitas: Latin for *Energy*
 - Bringing a new energy to power electronics
- Founded 2014 with HQ in El Segundo, CA
- Proven management team
 - 60+ employees
- Tier 1 manufacturing partners
 - TSMC wafer foundry, Amkor packaging
- Strong financial investors
 - Over \$1B capital under management



navitas
noun | en·er·gy

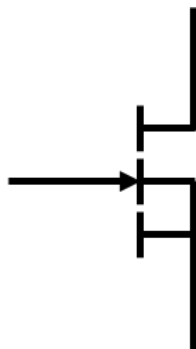




World's First GaNFast™ Power ICs

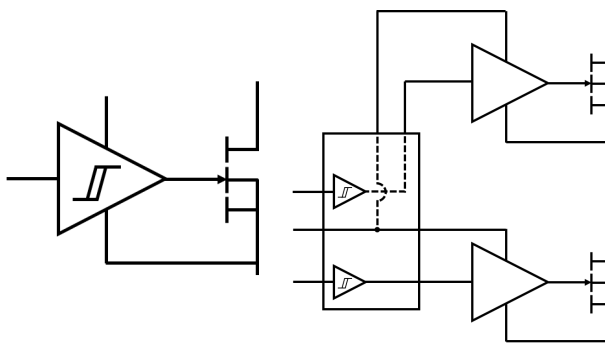


Fastest, most efficient
GaN Power FETs



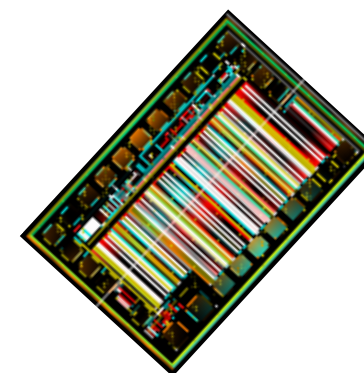
- >20x faster than silicon
- >5x faster than cascoded GaN
- Proprietary design
- Gate is fragile and sensitive to noise

First & Fastest Integrated
GaN Gate Drivers



- >3x faster than any other gate driver
- Proprietary design
- 30+ patents granted
- Fast, protected gate, no need for negative drive

World's First
GaNFast™
Power ICs



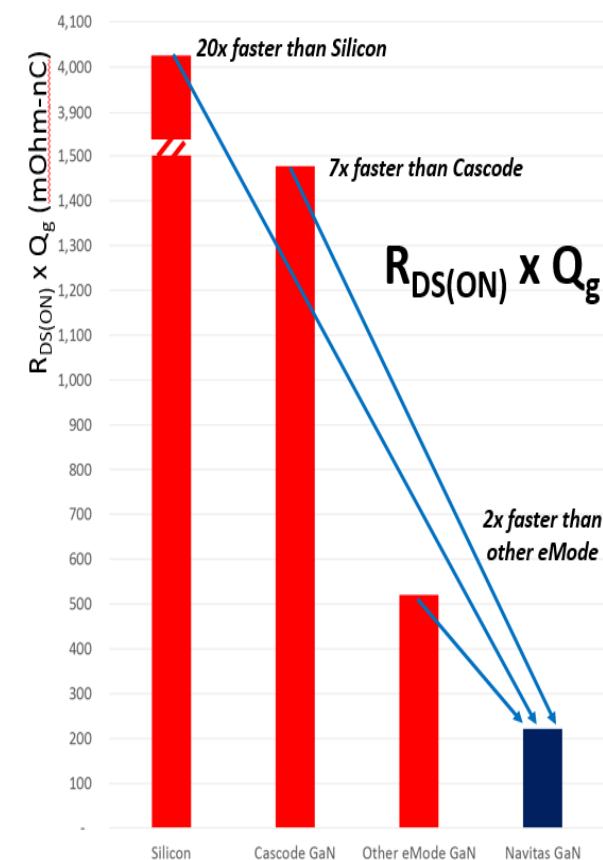
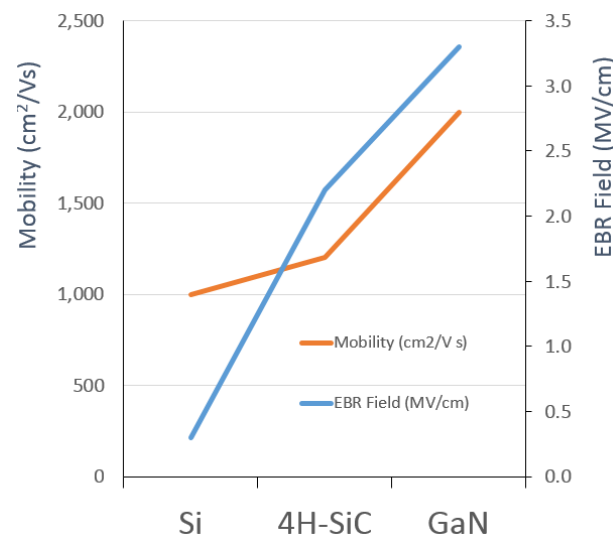
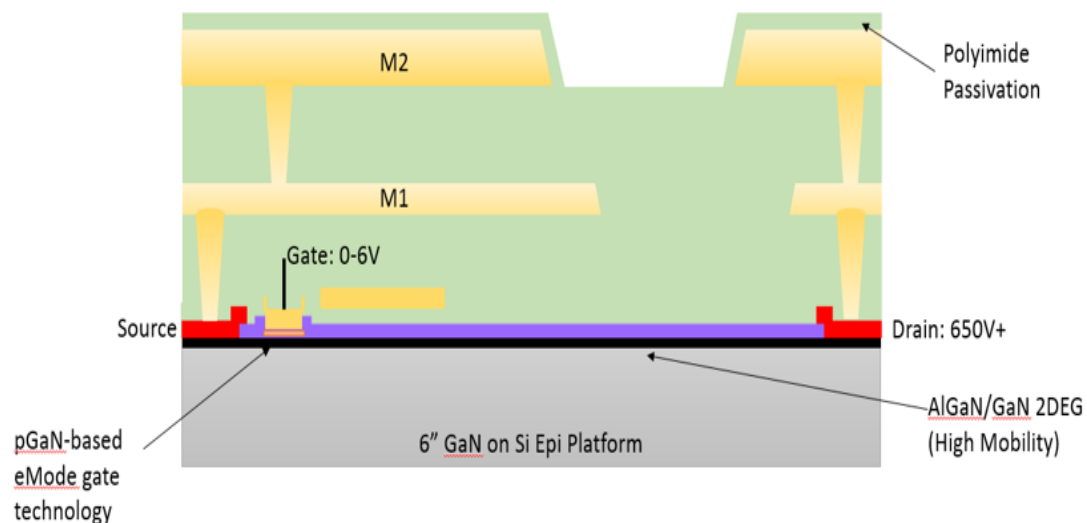
- Simple, fast and reliable
- Easy to use and package

Up to 40MHz switching, 5x higher density & 20% lower system cost



Navitas eMode Power FET Technology

GaNFast™



- Lateral device technology → Convenient isolation and easy voltage scaling
- High breakdown field (10X) and high mobility (2X) → Low $R_{DS(ON)}$, Low Q_{OSS}
- Lateral device technology → Low Q_g , easy to drive, easy to integrate
- Processed in established CMOS line → High yield, high capacity
- Multiple metal technology using standard CMOS processing equipment

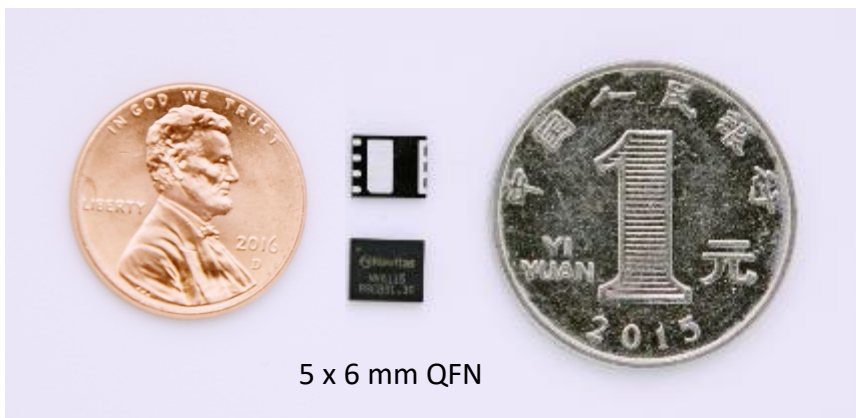


Single Switch GaN Power IC

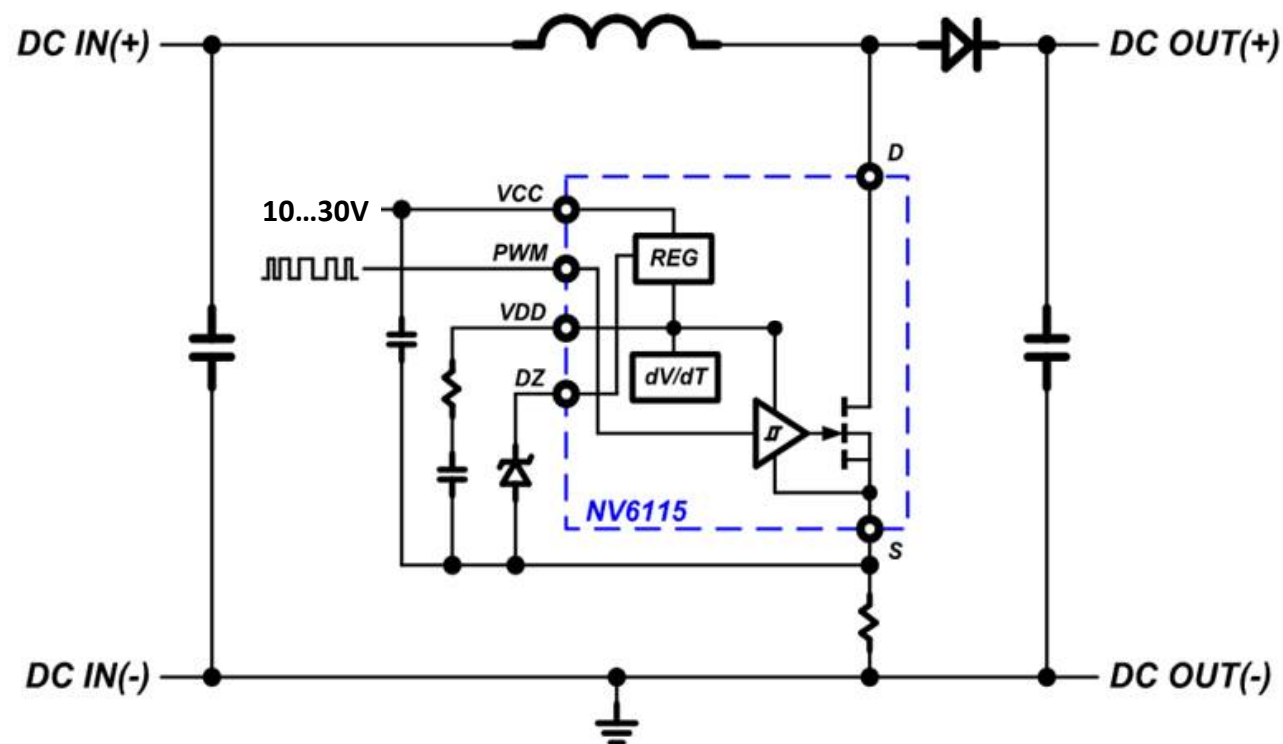
GaNFast™

Monolithic integration at 650V

- GaN FET (range 120-300 mΩ)
- GaN gate driver (fast, no overshoot)
- Wide input voltage range (10-30V)
- GaN regulator (well controlled gate voltage)
- dV/dt control (programmable 10-100V/nsec)
- Hysteretic input, ESD, fault protection
- Fast and controlled start-up

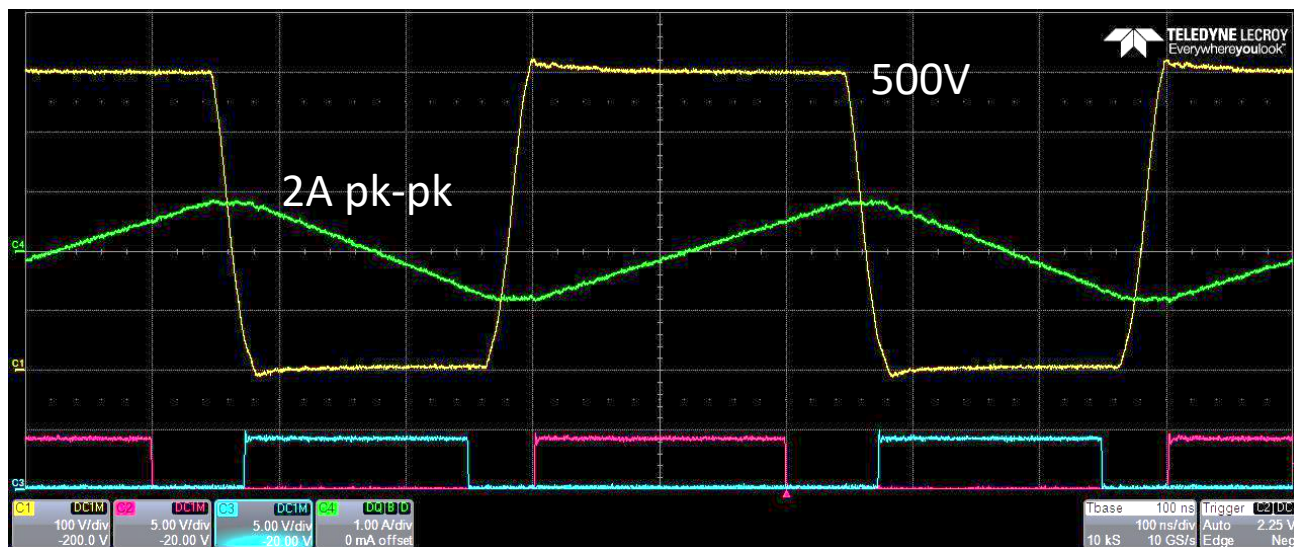


5 x 6 mm QFN



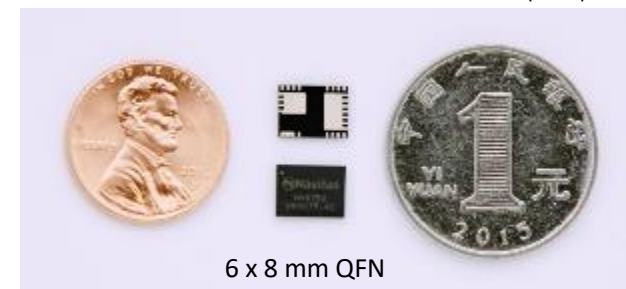
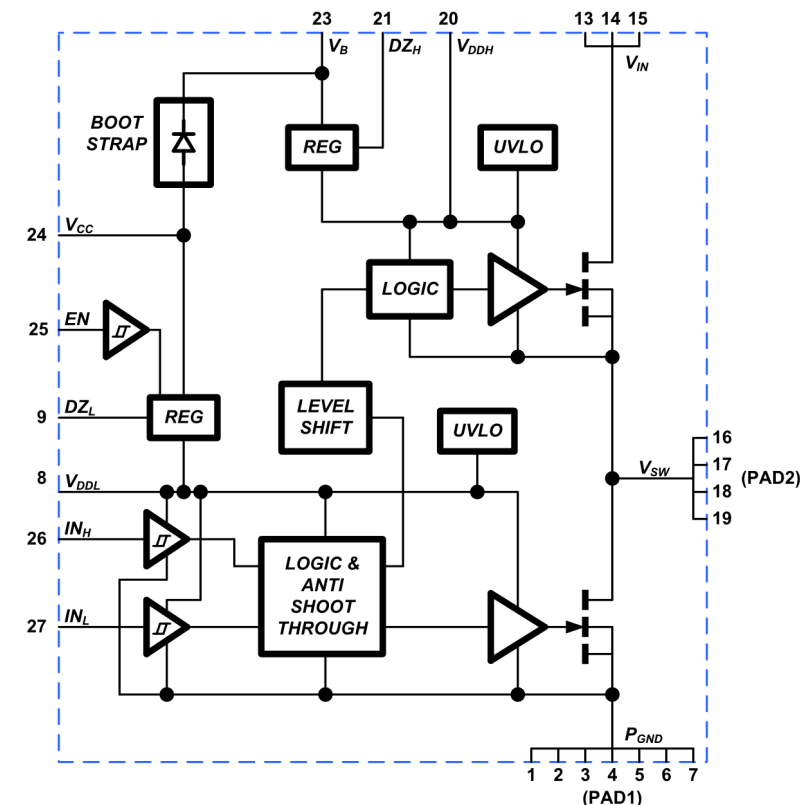


2 MHz Soft-Switching Operation



Monolithic integration at 650V

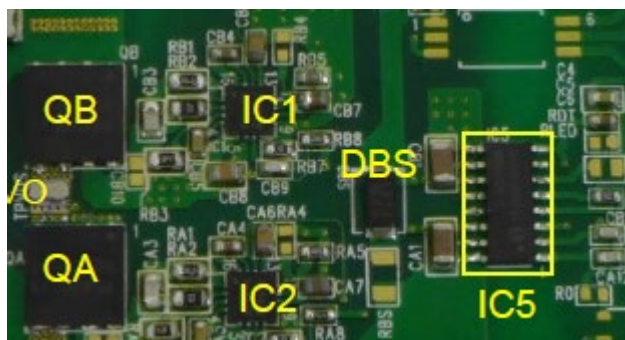
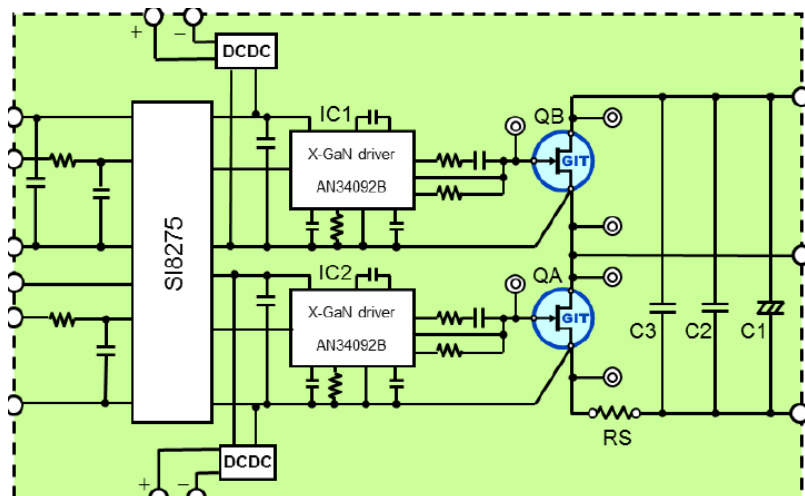
- 2x 650V eMode GaN FETs (α /symmetrical range 120-600 m Ω)
- 2x 6V GaN gate drivers
- 2x 30V to 6V GaN regulators and UVLO circuits
- 650V GaN level-shifters and bootstrap drivers
- GaN Logic (shoot-through protection, fault mgmt, ESD, etc...)





Complex Design → *Made Simple*

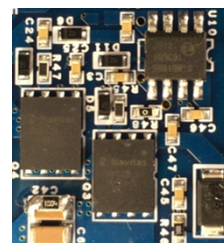
Half-Bridge *Discrete* GaN



PCB Area: 24 x 42 ~ 1,000 mm²

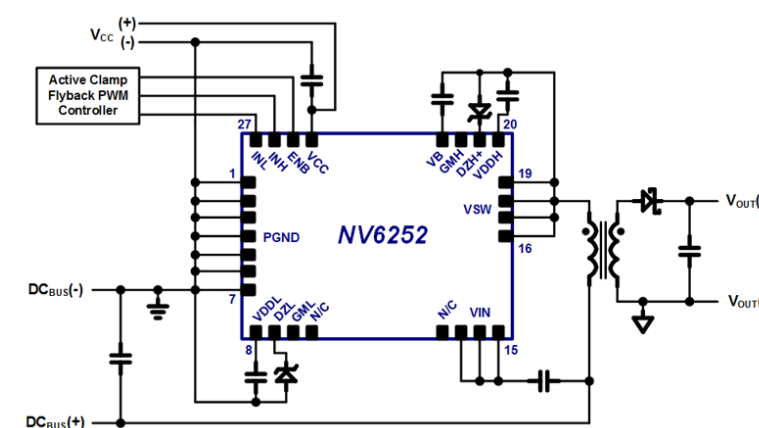
- 20x smaller PCB area
- 40+ fewer components
- Lower cost
- Robust & protected
- Simple
- Easy layout

Half-Bridge NV6115 GaN Power ICs + isolator and bootstrap diode



PCB Area: 18 x 20 = 360 mm²

Half-Bridge NV6252 GaN Power IC

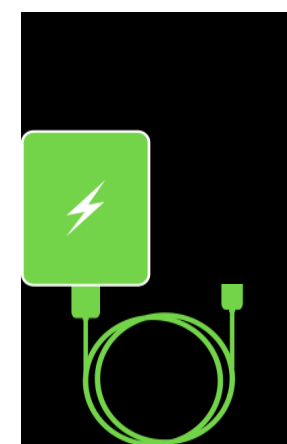
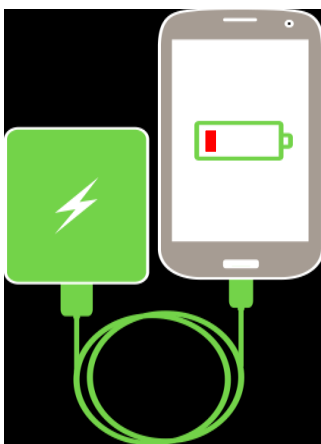
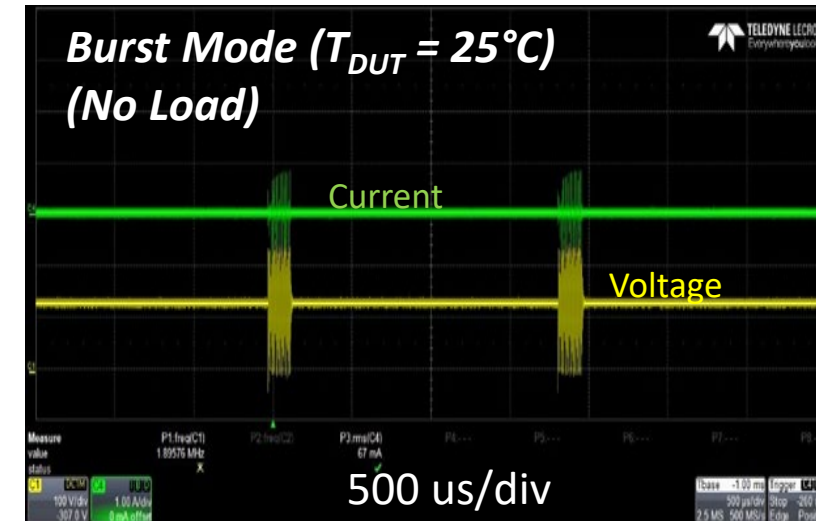
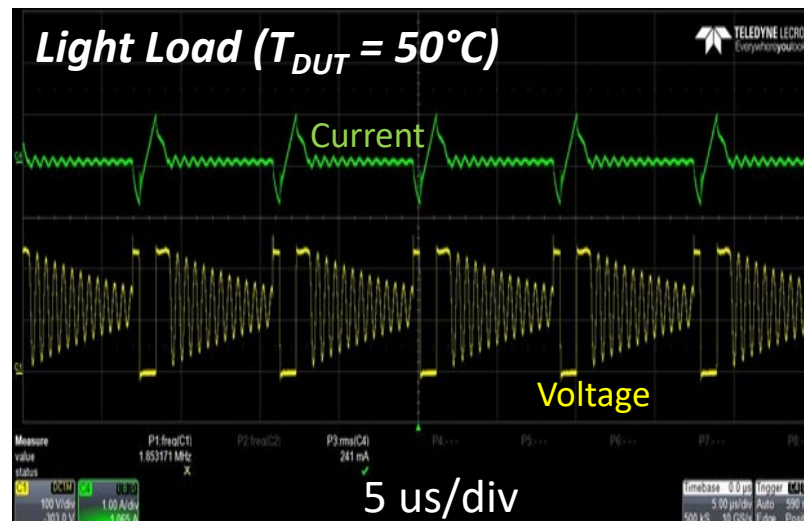
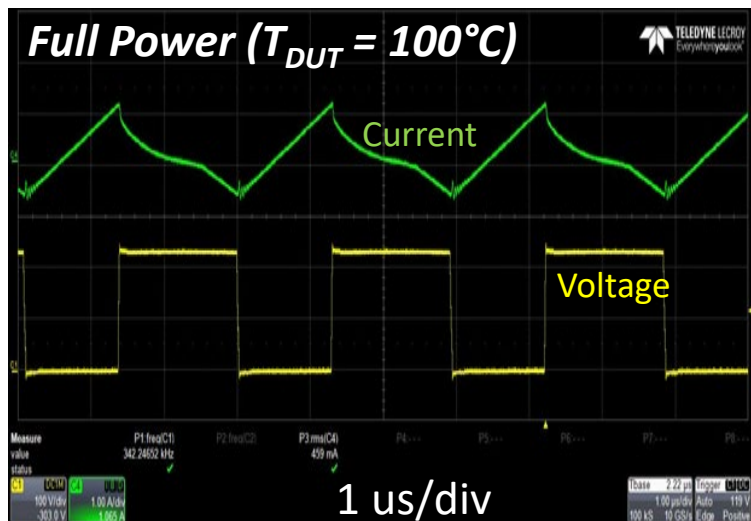


PCB Area: 6 x 8 = 48 mm²



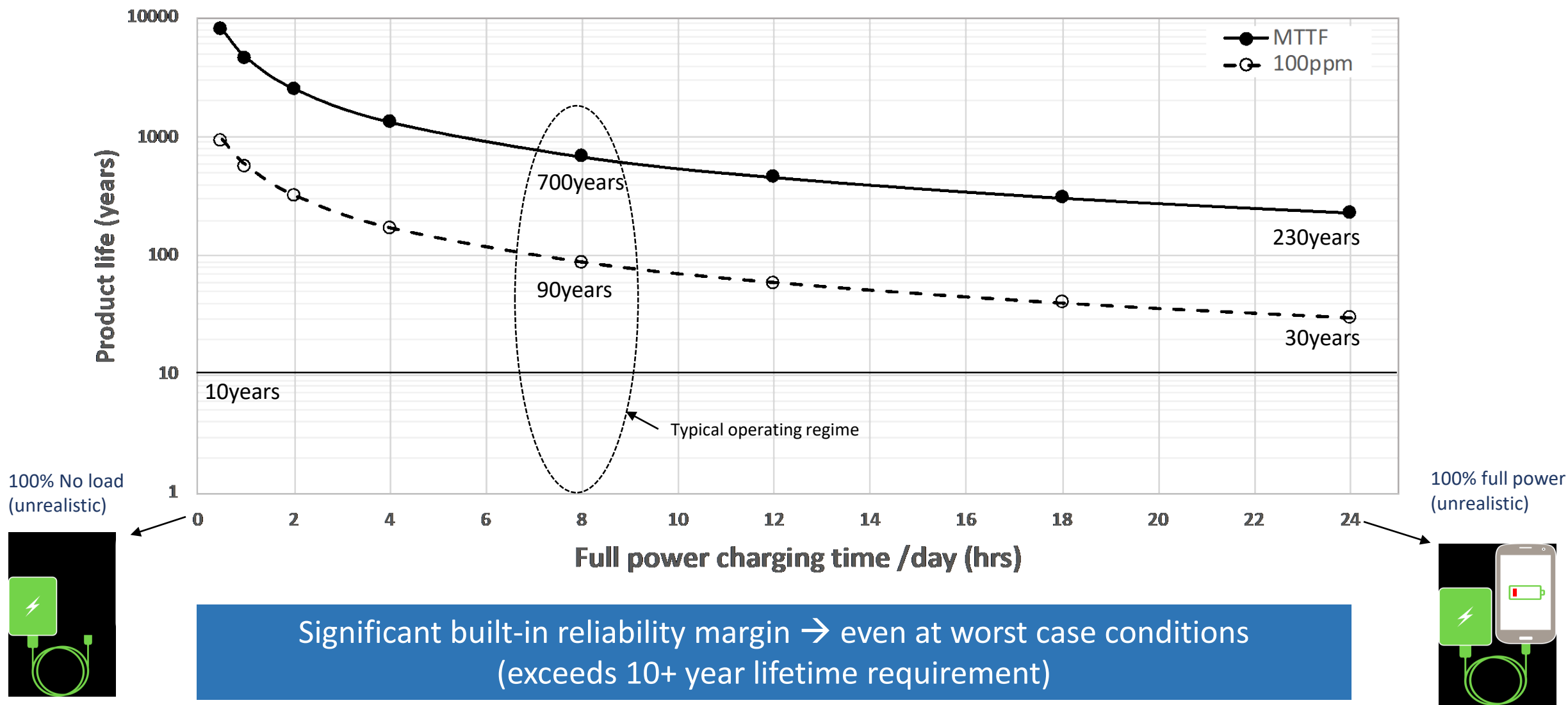
Application Profile for ACF Charger

GaNFast™





Lifetime Estimation in Charger Application





Reliability → Qualification → Release

GaNFast™

Reliability models
on IC building blocks
= Robust design

Mission profile
driven reliability =
Protected Customer

Comprehensive
reliability
monitoring

Reference	Test Conditions	Duration	Lots	S.S.	
JESD22-A113 J-STD-020	Preconditioning (MSL1): Moisture Preconditioning + 3x reflow: HAST, UHAST, TC & PC	N/A	3	308	PASS (0/308)
JESD22-A104	Temperature Cycle: -55°C / 150°C	1,000cy	3	77	PASS (0/231)
JESD22-A122	Power Cycle: Delta Tj = 100°C	10,000cy	3	77	PASS (0/231)
JESD22-A110	Highly Accelerated Stress Test: 130°C / 85%RH / 100V V _{DS}	96hrs	3	77	PASS (0/231)
JESD22-A108	High Temperature Reverse Bias: 150°C / 520V V _{DS}	1,000hrs	3	77	PASS (0/231)
JESD22-A108	High Temperature Gate Bias: 150°C / 6V V _{GS}	1,000hrs	3	77	PASS (0/231)
JESD22-A108	High Temperature Operating Life	1,000hrs	3	77	PASS (0/231)
JESD22-A108	Early Life Failure Rate	24 hrs	3	1,000	PASS (0/3,000)
JS-001-2014	Human Body Model ESD	N/A	1	3	PASS 0/3
JS-002-2014	Charged Device Model ESD	N/A	1	3	PASS 0/3

Metric	Results
Equivalent device hours tested*	1.5 billion hours
FIT*	0.6

*Statistics calculated from HTOL tests

GaNFast™

POWER ICs

Quality

Speed

Efficiency

Now in high volume production!



PowerAmerica Project Objectives



Project Title:

65W High-Efficiency High-Density Adapter with Improved Manufacturability

Objectives:

Create a commercially compelling platform that sets an industry standard in energy efficiency, power density & is manufacturing proven & volume ready (TRL $\geq$ 8) for US OEMs.

Major Milestones:

Aug 2017 – 1st proto

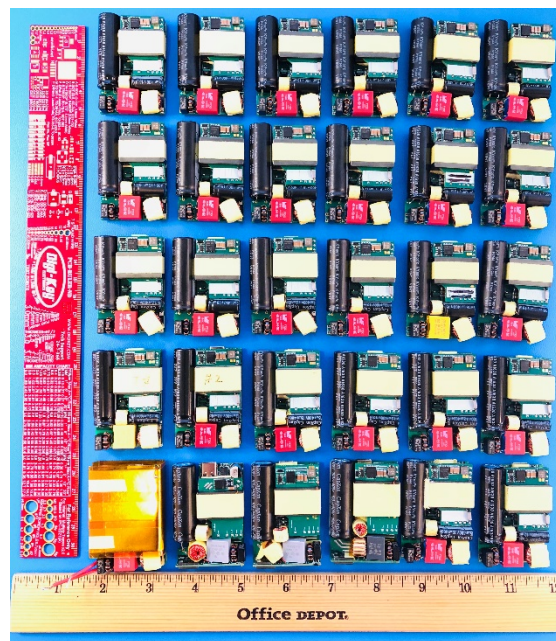
Nov 2017 – eval & optimization

Feb – final design

May – manufacturing validation

Deliverables:

30 adapter ref designs



1. Advances over silicon or conventional approaches: *Advancement & commercialization of Navitas GaN power ICs*

2. Markets impacts: *mobile chargers, travel adapters (consumer electronics)*

3. Timeframe for commercialization: *Q3 2018*

4. Quantitative benefits over state-of-the-art: *50% higher density, 30% improved energy efficiencies, improved manufacturability at a lower cost per watt*

5. Impact on the cost of WBG compared to Silicon: *A high-volume platform that demonstrates WBG superiority over silicon in performance and cost*

6. Potential for Job Creation Economic impact: *Significant job creation for US manufacturing partner(s) & US OEMs*

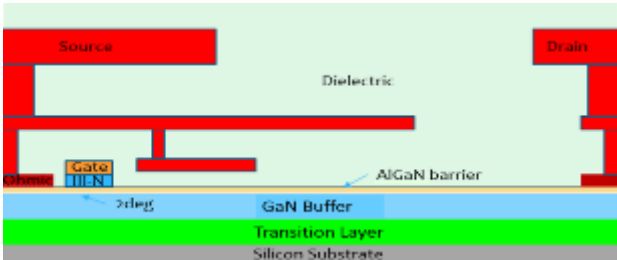
7.. Workforce Development and Education: *All R&D and manufacturing is 100% based in the US with significant workforce development and education with Navitas, suppliers, partners and customers*



Key Elements For New Adaptors

High Power Density Adaptors Needs

- GaN Power Device
- Higher Integration
- Advanced Magnetics
- High Frequency Controllers
- Soft Switching Topologies



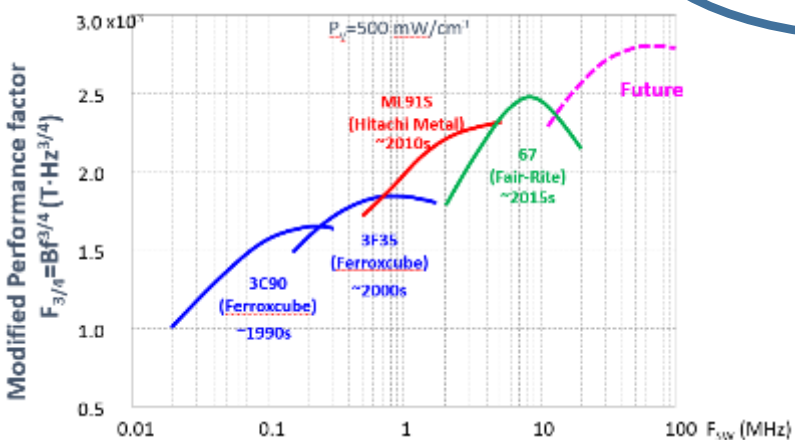
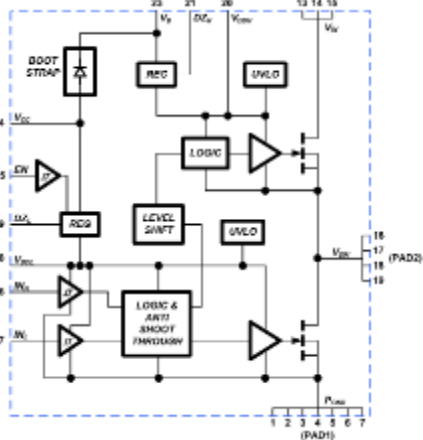
Higher
Integration

GaN
Power
Device

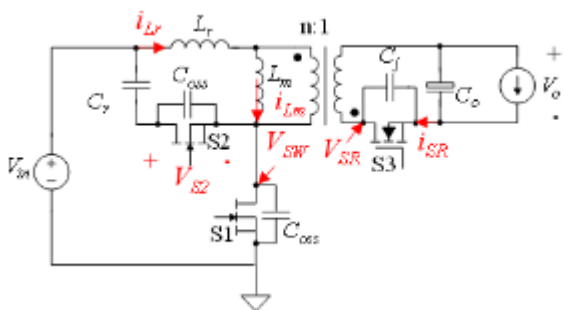
New
Magnetics

New
Control IC

New
Topology

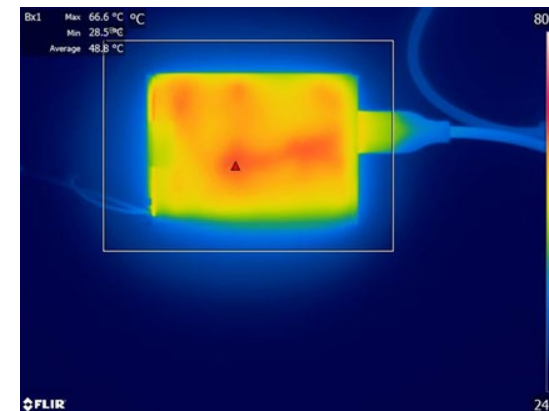
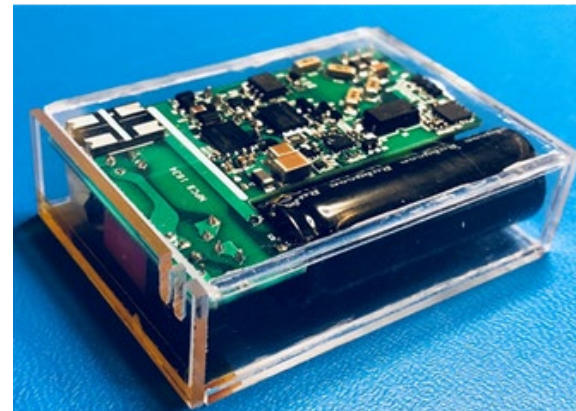
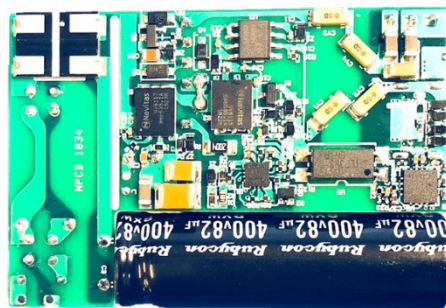
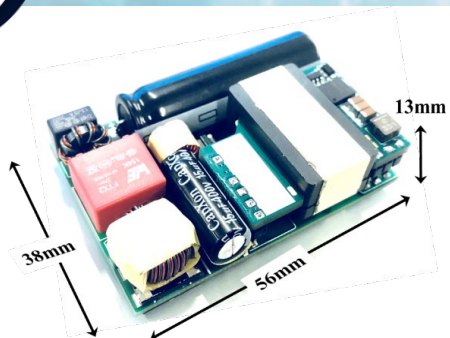


>500Khz controllers
are ready!





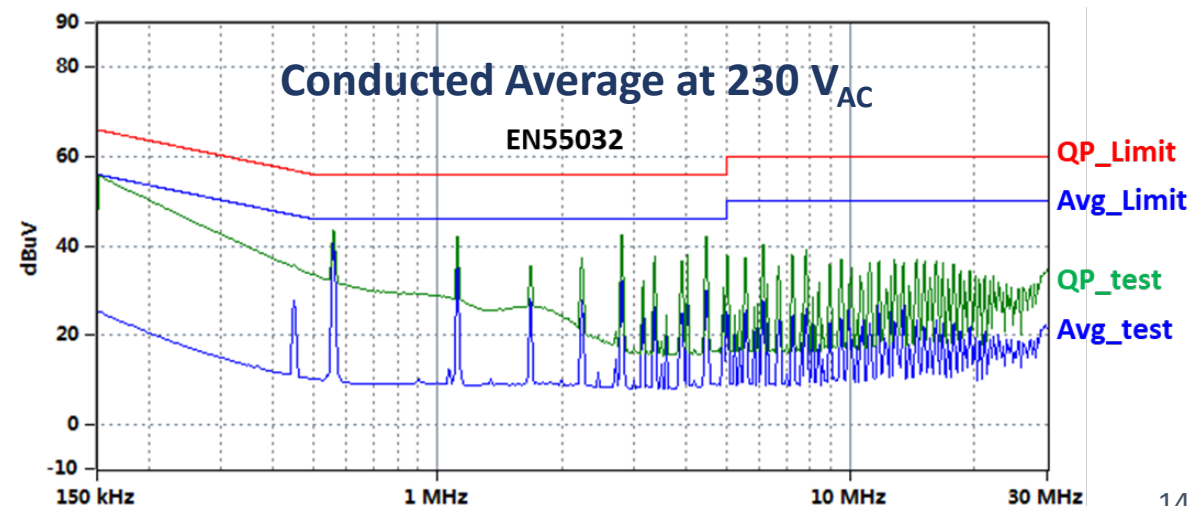
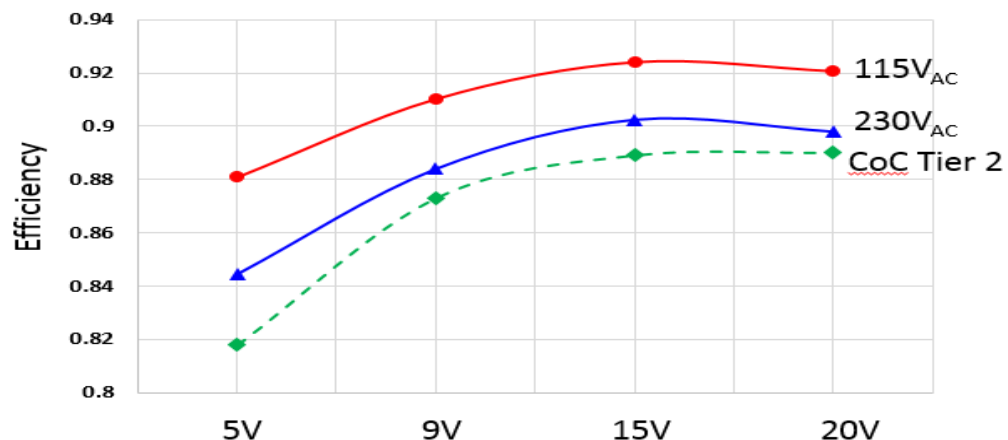
World's Smallest 65W USB-PD



Power, Output	65 W USB-PD
Topology	ACF with NV6115, NV6117 GaNFast Power ICs
Frequency	600 kHz
Size	27 cc (45 cc with case)
Density	2.4 W/cc (39 W/in ³) uncased 1.5 W/cc (24 W/in ³) cased
Efficiency	93.3% peak (115 V _{AC}) 93.2% at 90 V _{AC} full load DoE Level VI, Euro CoC (EuP) Tier 2

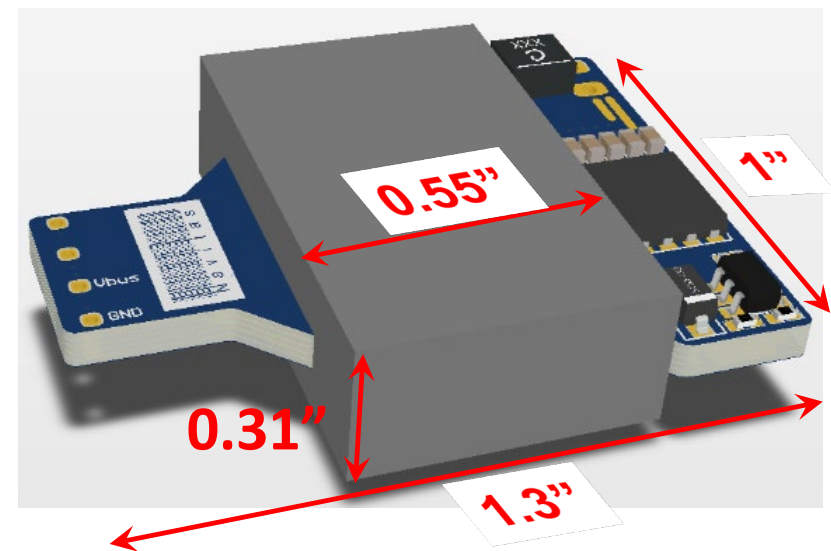
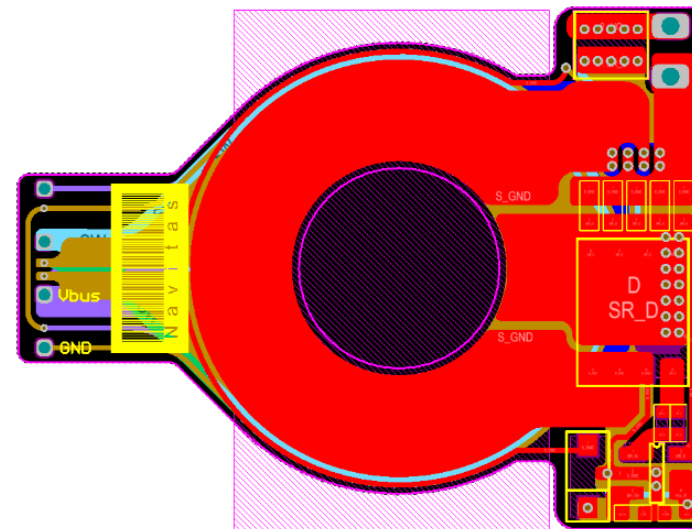
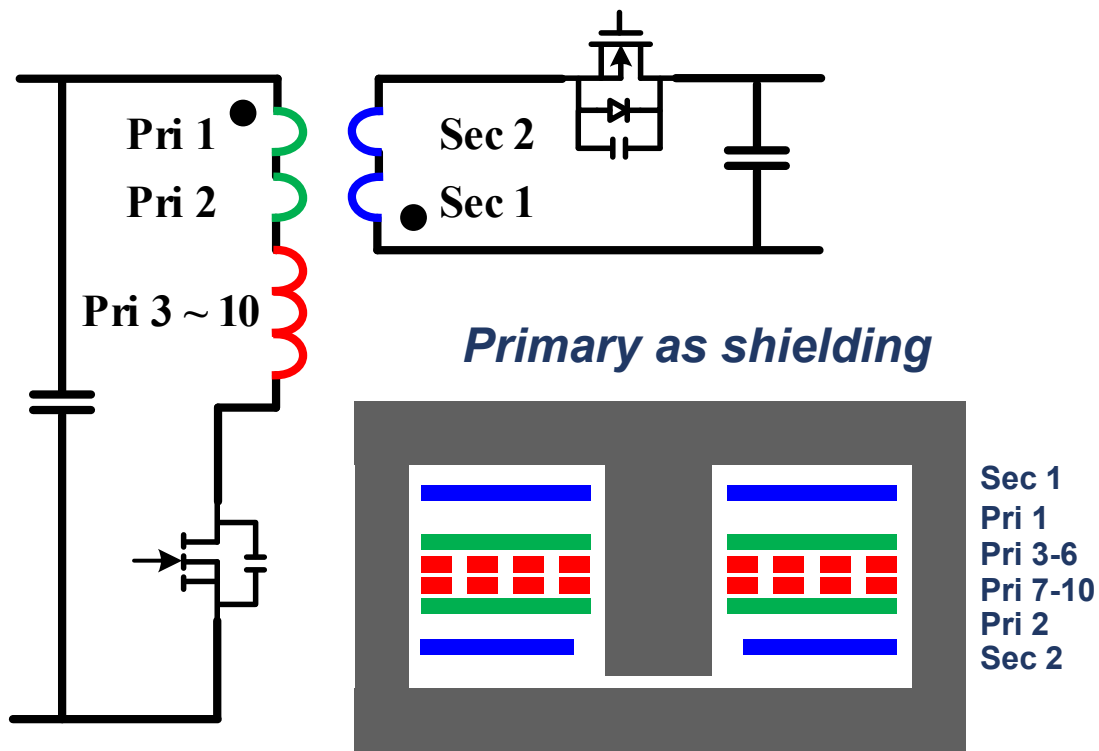
115 V_{AC}, 20 V / 3.25 A, 25°C ambient, no case, no airflow, no heatsink
20mins steady state operation. Maximum case <70°C

4-Point Average Efficiency





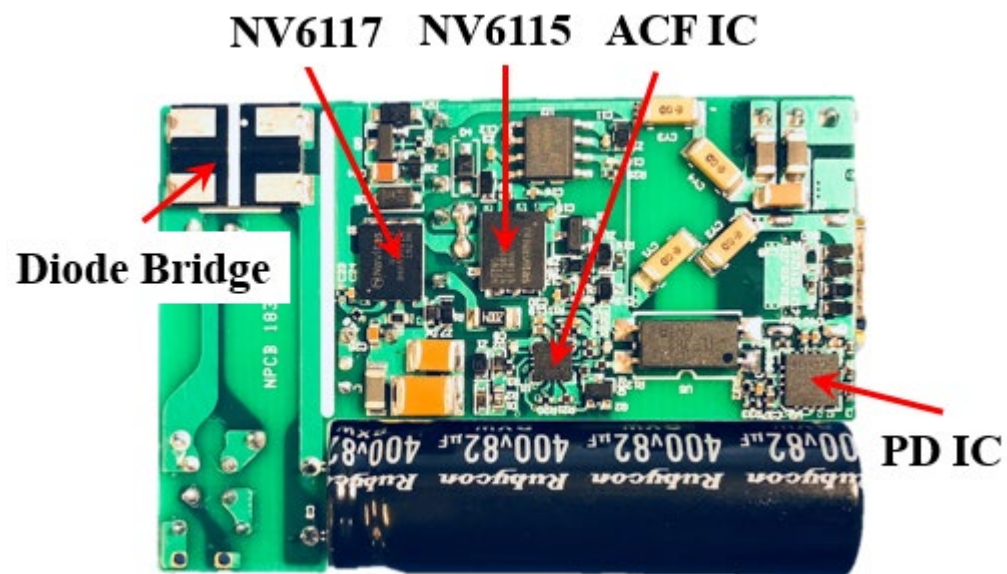
High Frequency Magnetics → Made Manufacturable



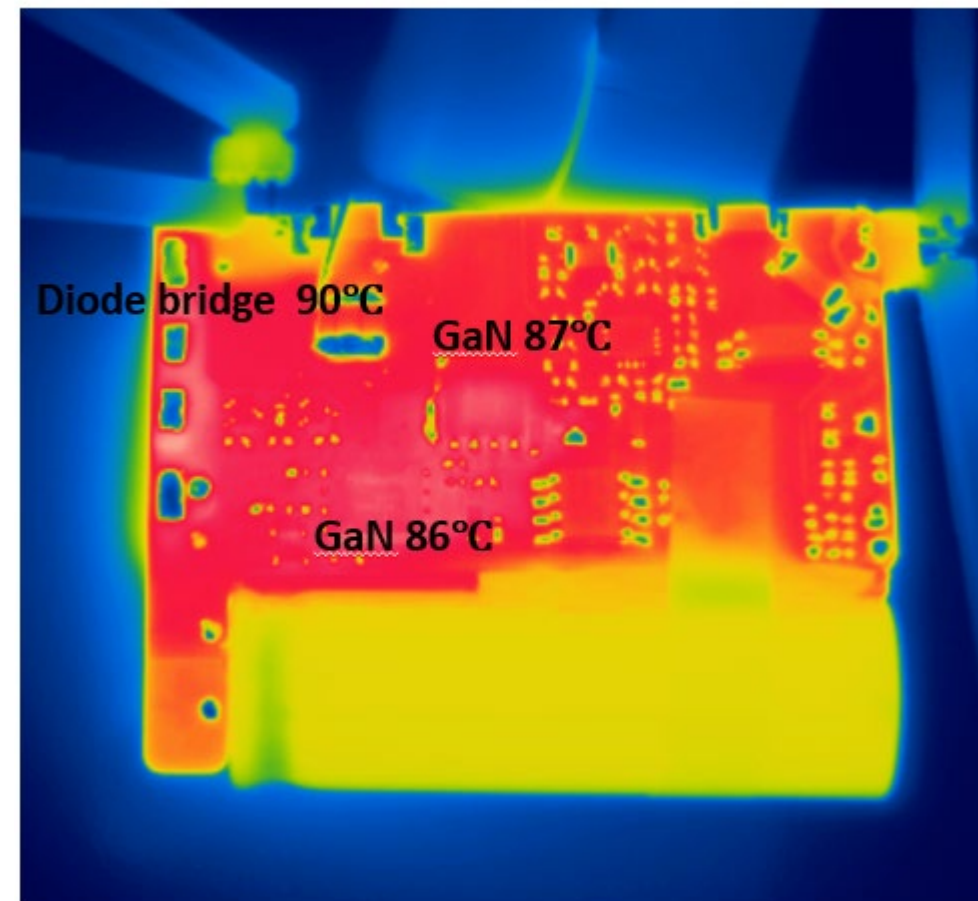
- SR on secondary winding, minimized L_k & R_{ac}
- Shielding integrated as primary winding
- Safety rule compliance



Design Details & Thermal Performance



65W/90Vac



Component max temperature is 90°C



Accomplishments & Outcomes

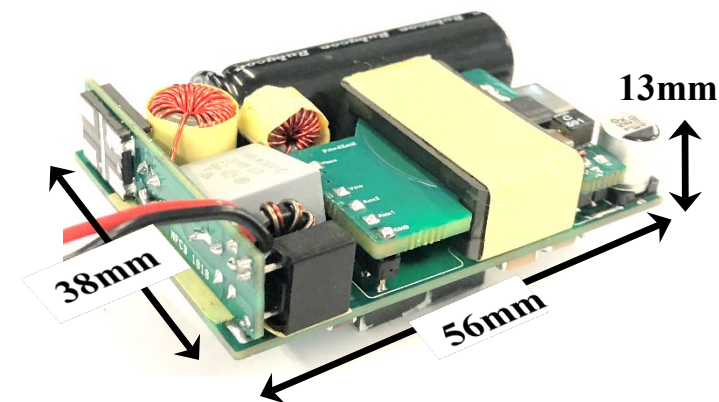


- **Accomplishments**

- Completed 65W design
 - Verified efficiency, density, thermal, EMI, etc.
- Technology platform adopted and released to production
 - World's thinnest universal 45W adapter ([Mu One](#))

- **US Manufacturing Impact**

- Reduced labor content, costs
 - Fully automated transformer, reduced component count
- Reduced manufacturing costs
 - Improved manufacturing quality & consistency (yield)
 - Automated transformer assembly
 - Reduced re-work
- Significant US OEM interest to drive global adoption



PowerAmerica Project:
65W USB-PD 3.0, 27 cc, 2.4 W/cc (39 W/in³)



Commercial realization: Mu One
45W USB-PD 3.0, only 14 mm thin cased



Existing: “The Mu”



- 14 mm profile
- CE, UL, etc.



- 90-264 V_{AC} input
- 2 x 6 W = 12 W (Type A)

Images courtesy Made-in-Mind



Challenge: Fast Charging “Mu One”



- 14 mm profile
- CE, UL, etc.

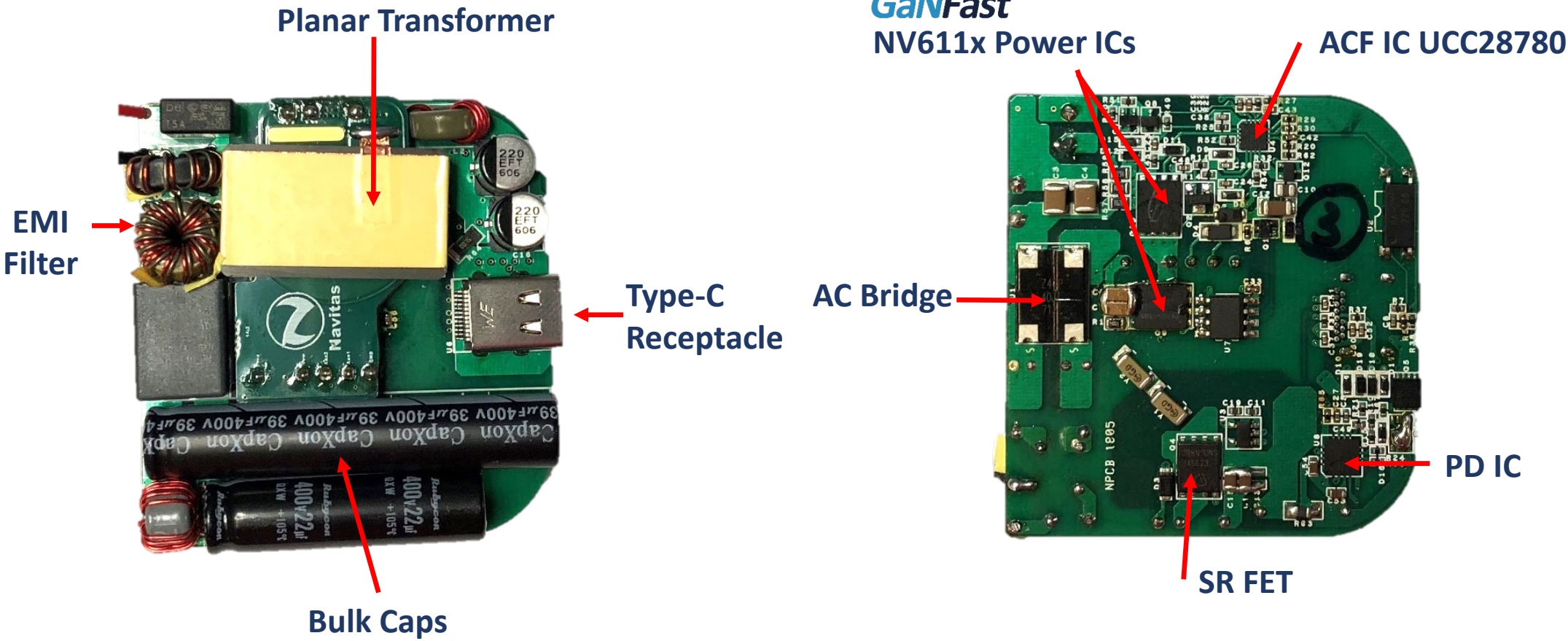
Images courtesy Made-in-Mind



- 90-264 V_{AC} input
- ~~2 x 6 W = 12 W (Type A)~~
45 W (USB-PD Type C)



45 W in 11 mm = HF Planar ACF





Cool Operation

Top

Bottom

GaNFast
Power IC 75°C, 80°C

AC Bridge 80°C

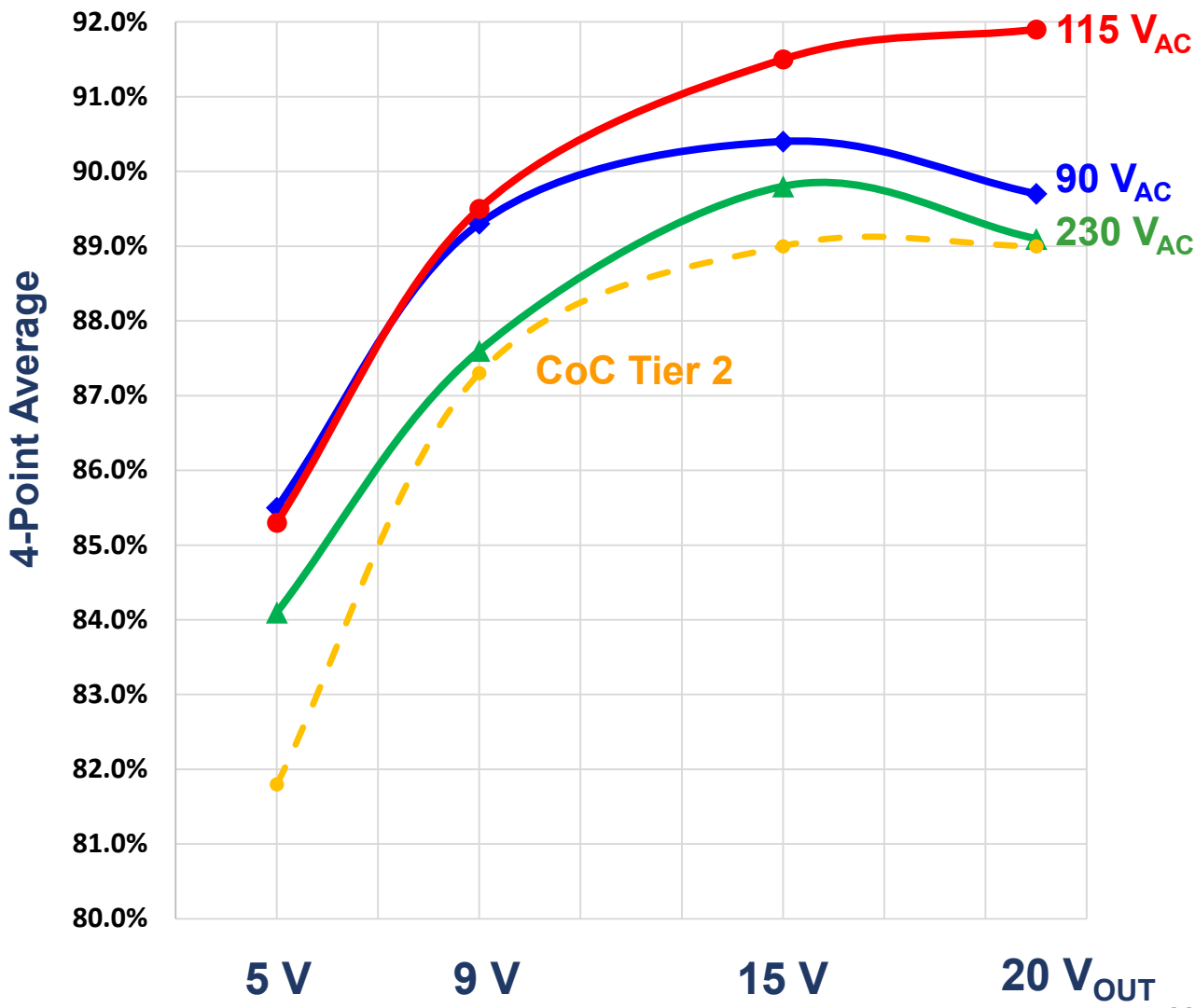
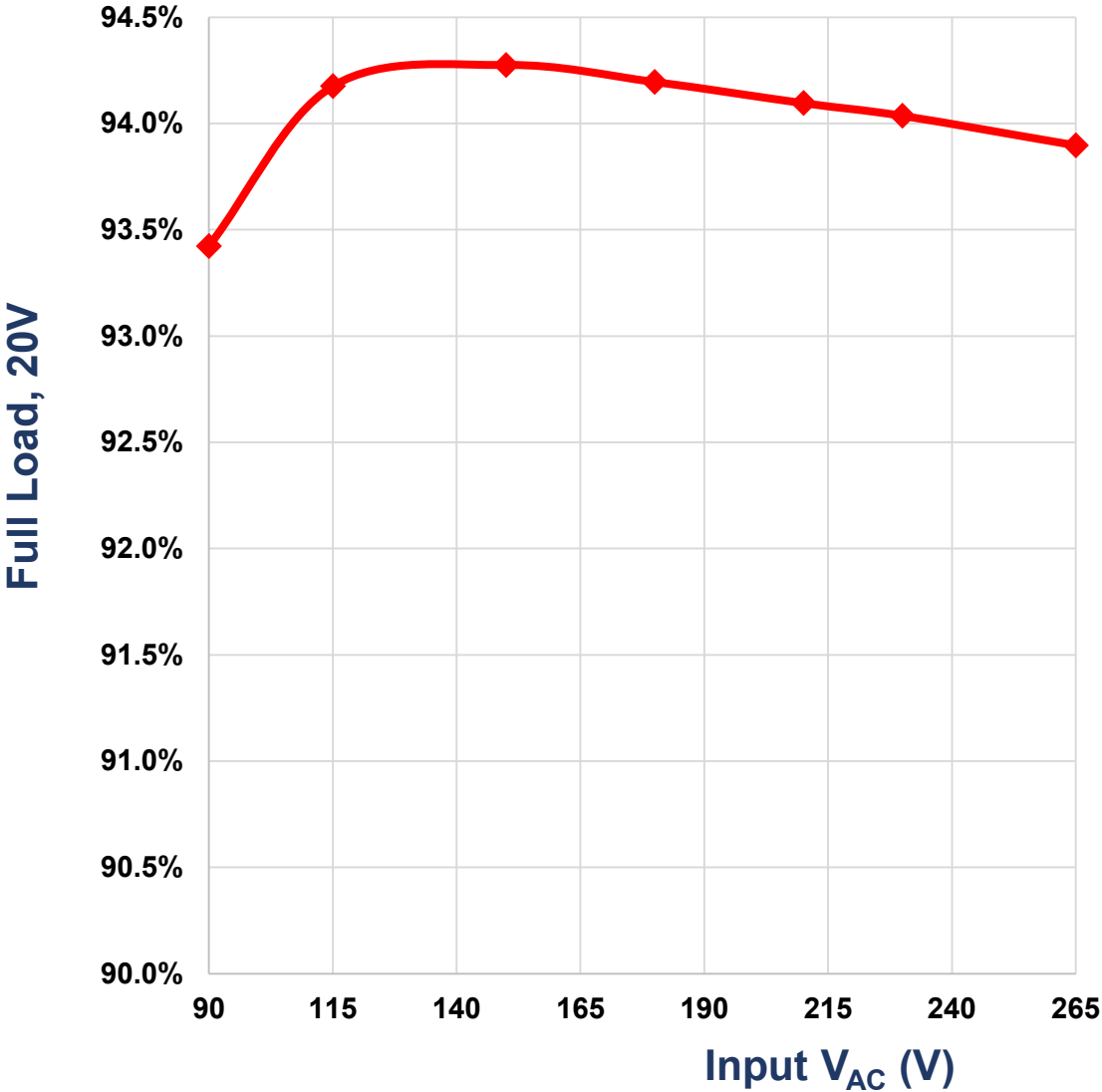
SR IC 85°C
SR FET 85°C

Transformer 80°C

90 V_{AC}, 45 W, 25 °C, uncased, no airflow,
no thermal compound / heatsinking

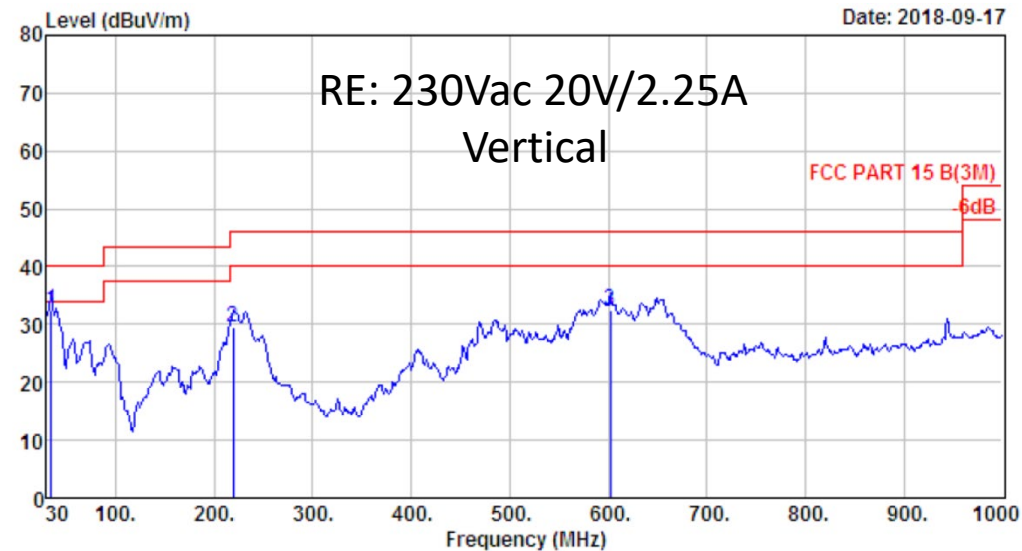
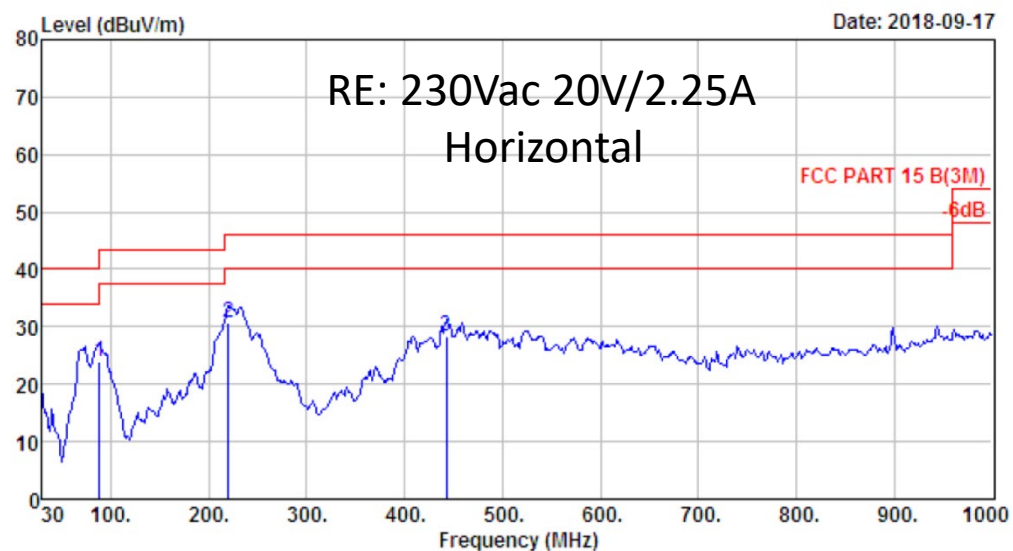
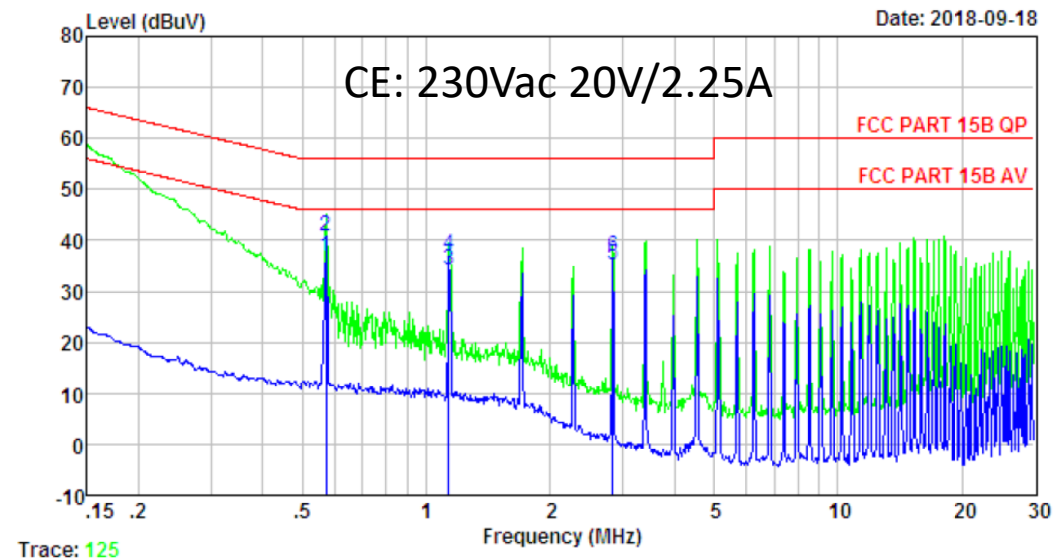
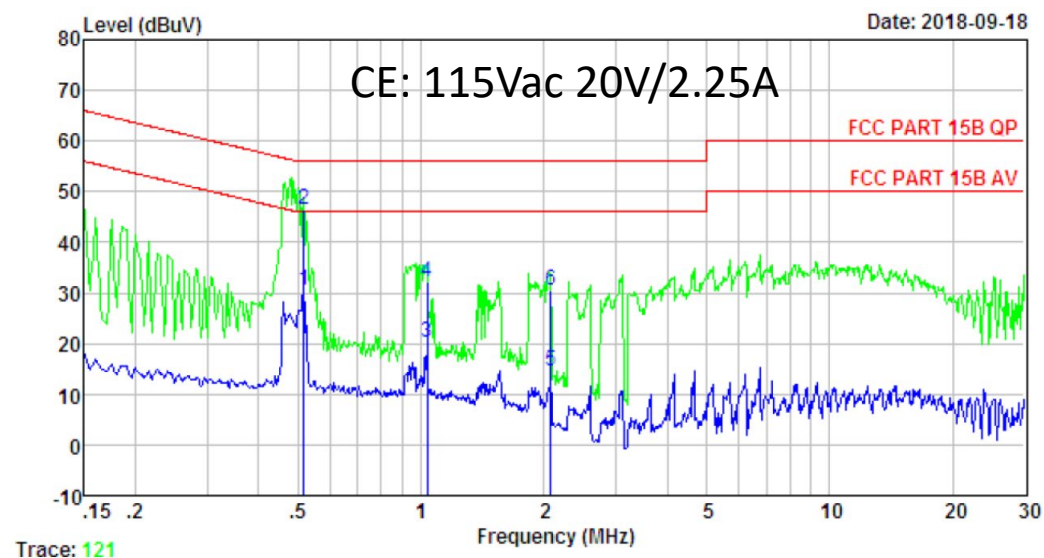


High Efficiency Across Line, Load, Output Voltage



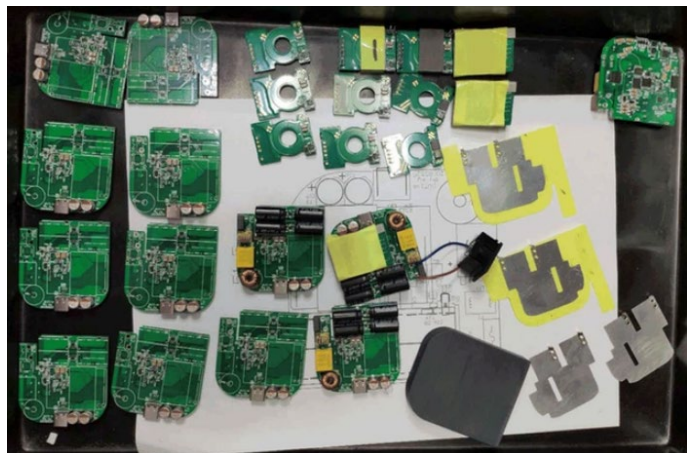


Quiet EMI (Conducted, Radiated)





Mu One: From Prototype to Mass Production



- Thanks to Matt Judkins, CEO of Made-in-Mind (Mu One)
- Available via www.kickstarter.com and www.amazon.com and airport stores

Images courtesy Made-in-Mind



RAVPower 45W: Same Platform

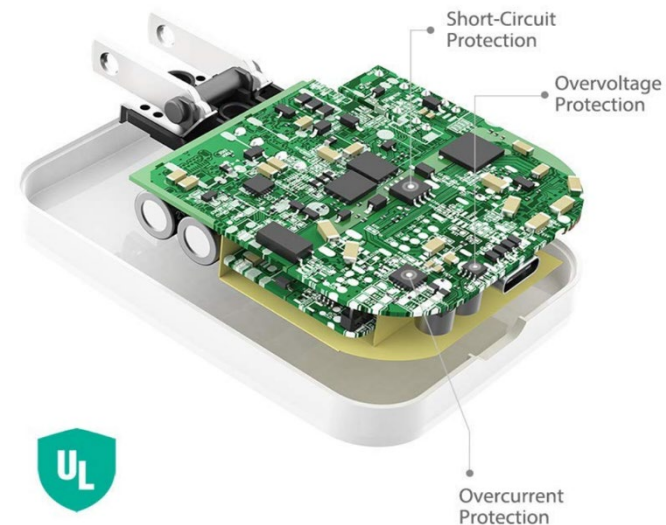
**45W Power Delivery
2.5X Faster**



Macbook 12"
2.0 hrs

iPhone XS Max
1.8 hrs

NOTE: Cable not included



Available now on www.amazon.com

RAVPower



RAVPower

New Logo. New Image.
A Leap In Power Like Never Before.

Images courtesy RAVPower



AUKEY USB-C GaNFast Chargers



27W USB-C



12W x 2 USB-A



27W USB-C

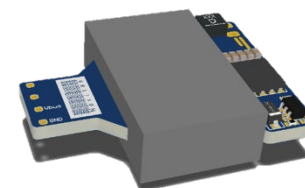
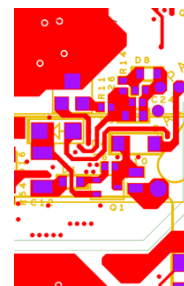
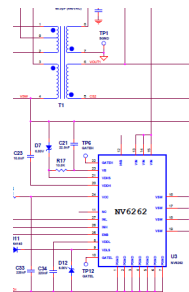
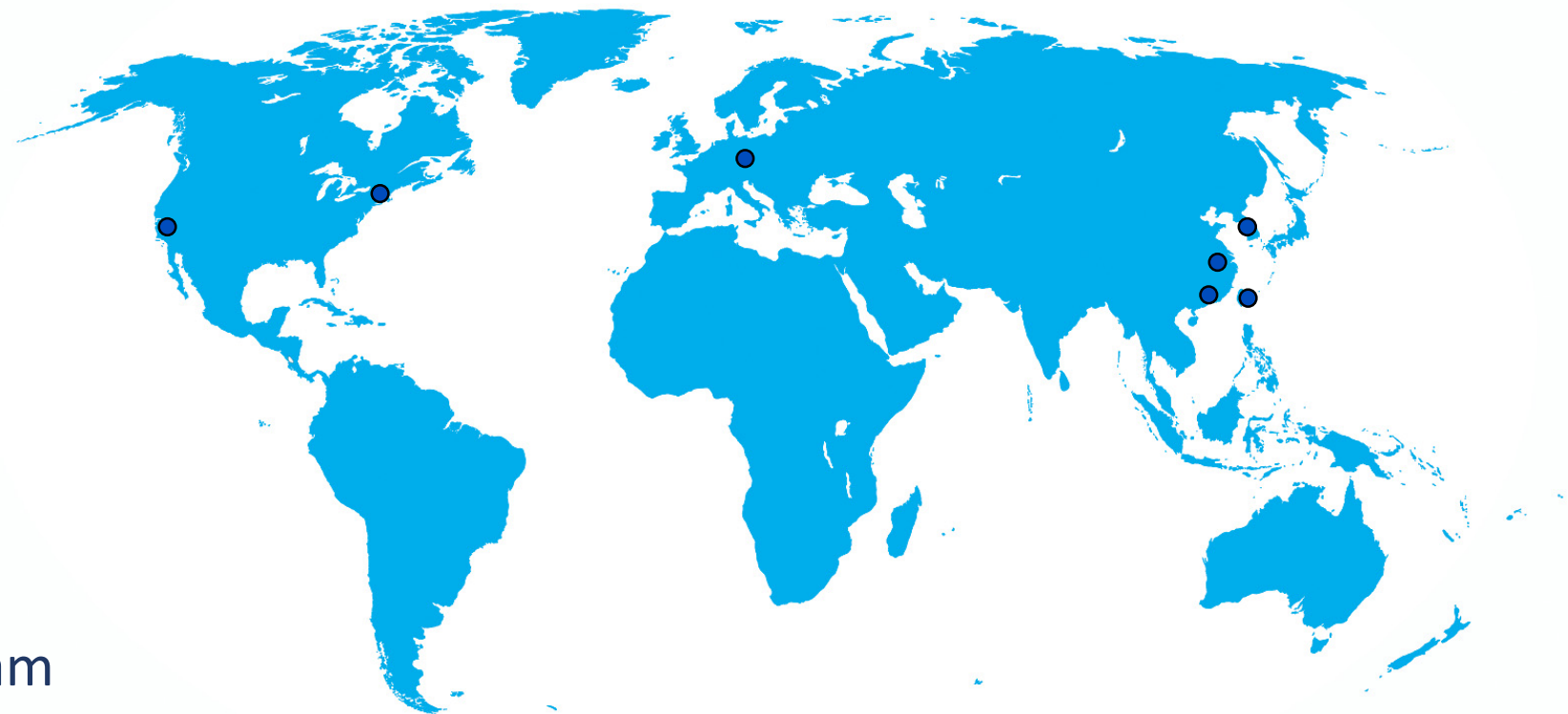
Available now on www.amazon.com

Images courtesy AUKEY



GaNFast Design Support

- Global technical support
 - Direct support
 - Partner support (VAR)
- Strong AE team
- Strong FAE team
- GaNFast Design Support Program
 - From schematic to EMI
 - Components, magnetics, PCB
 - Critical component support
 - System reliability support





GaNFast™



Let's go **GaNFast™**